



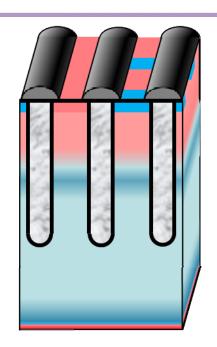


For Further Growth Together

Field Stop IGBT

General Description

- ·Available in 6" wafers
- Fine Cell Pitch and optimized Emitter structure → Good balance of DC and AC performances
- Deep Trench Gate
 - → Low Vcesat



Product Summary

VCES	IC	VCESAT	Eoff
650V	40A	1.5V typ	0.5mJ
1200V	40A	2.2V typ	1mJ
1200V	75A	2.2V typ	2mJ
			@Ti=25℃

Road Map

2(0)2(3)2024 2025 2026 2027RS MP 650V/40A ₩RS ₩P 1200V/75A ⇔RS ⊕MP 1200V/40A